

RJP30H2DPK-M0

Silicon N Channel IGBT
High speed power switching

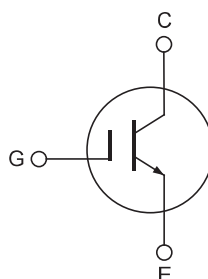
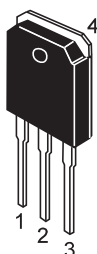
R07DS0467EJ0200
Rev.2.00
Jun 15, 2011

Features

- Trench gate and thin wafer technology (G6H-II series)
- Low collector to emitter saturation voltage: $V_{CE(sat)} = 1.4 \text{ V typ}$
- High speed switching: $t_f = 100 \text{ ns typ}$, $t_r = 180 \text{ ns typ}$
- Low leak current: $I_{CES} = 1 \mu\text{A max}$

Outline

RENESAS Package code: PRSS0004ZH-A
(Package name: TO-3PSG)



1. Gate
2. Collector
3. Emitter
4. Collector (Flange)

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to Emitter voltage	V_{CES}	360	V
Gate to Emitter voltage	V_{GES}	± 30	V
Collector current	I_c	35	A
Collector peak current	$i_{c(peak)}$ ^{Note1}	250	A
Collector dissipation	P_C ^{Note2}	60	W
Junction to case thermal impedance	θ_{j-c}	2.08	$^\circ\text{C}/\text{W}$
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

- Notes: 1. $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$
2. $T_c = 25^\circ\text{C}$